

Notice of References Cited	Application/Control No. 10/671,233	Applicant(s)/Patent Under Reexamination ZHAO, JIAN H.	
	Examiner TAN N. TRAN	Art Unit 2826	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Zhao et al., "Demonstration of a high performance 4H-SiC vertical junction field effect transistor without epitaxial regrowth", Feb. 2003, pp. 321-323, Electronics Letters, IEEE, Stevenage, SG1 2SD, UK.
	V	
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